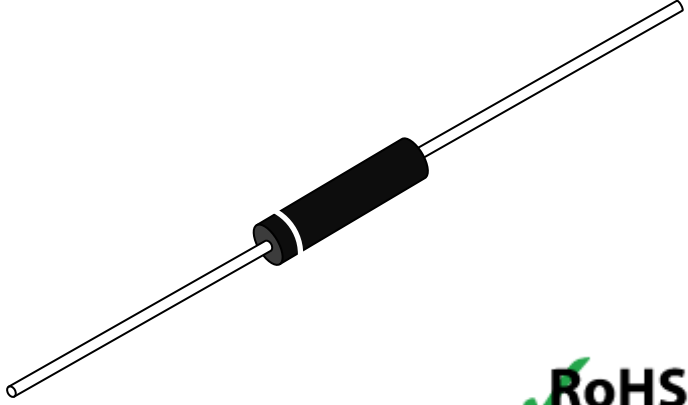
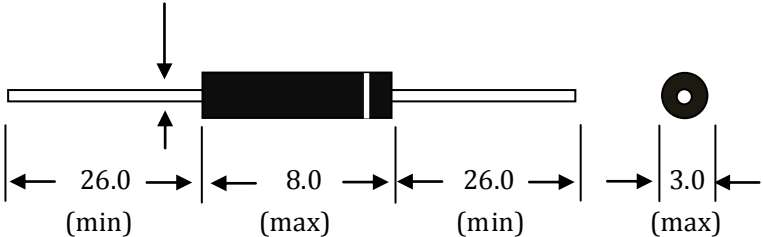


Introduce:	Reference Shape:
HVGT high voltage silicon rectifier diodes is made of high quality silicon wafer chip and high reliability epoxy resin sealing structure, and through professional testing equipment inspection qualified after to customers.	
Features:	
Fast recovery. High reliability design. Low current, high voltage. Conform to RoHS and SGS. Epoxy resin molded in vacuumHave anticorrosion in the surface.	



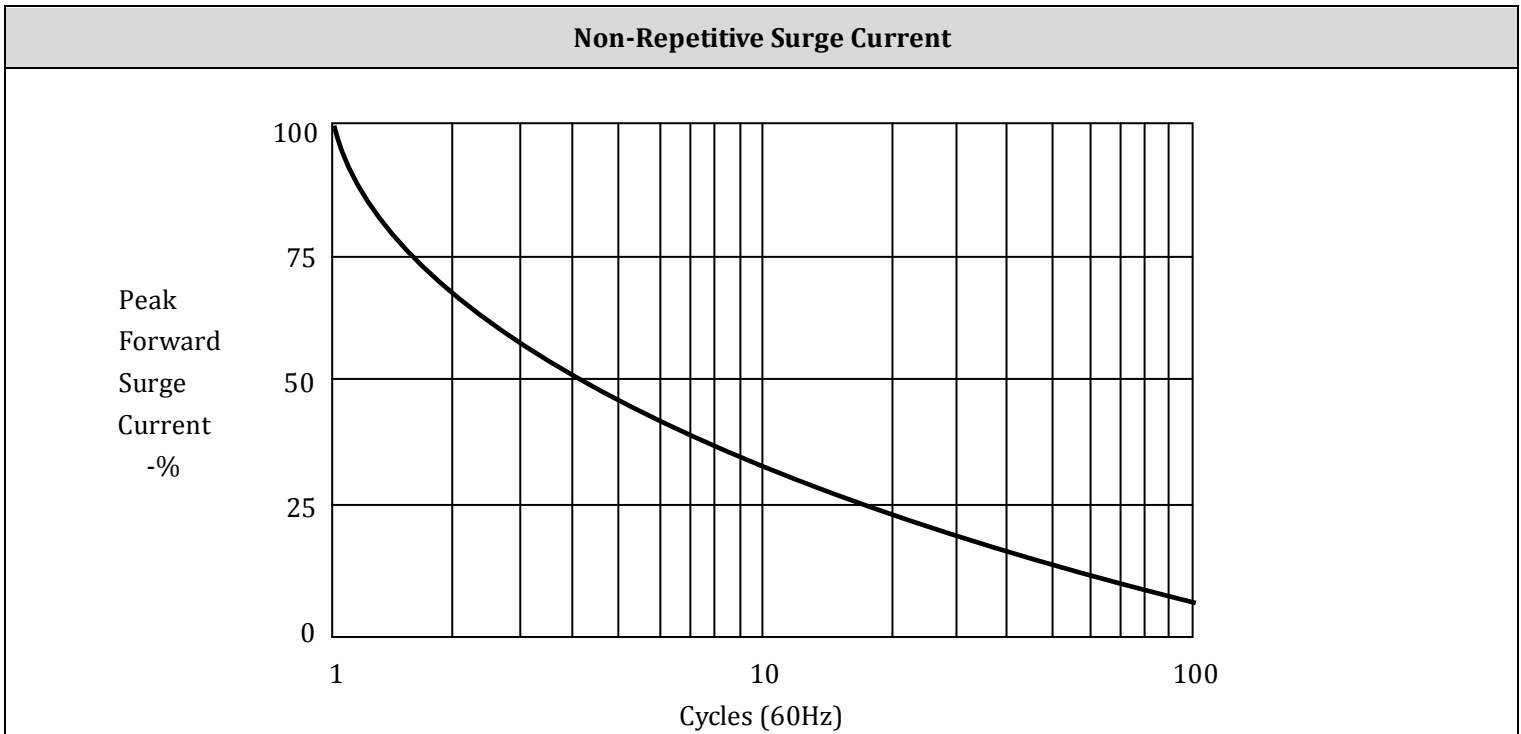
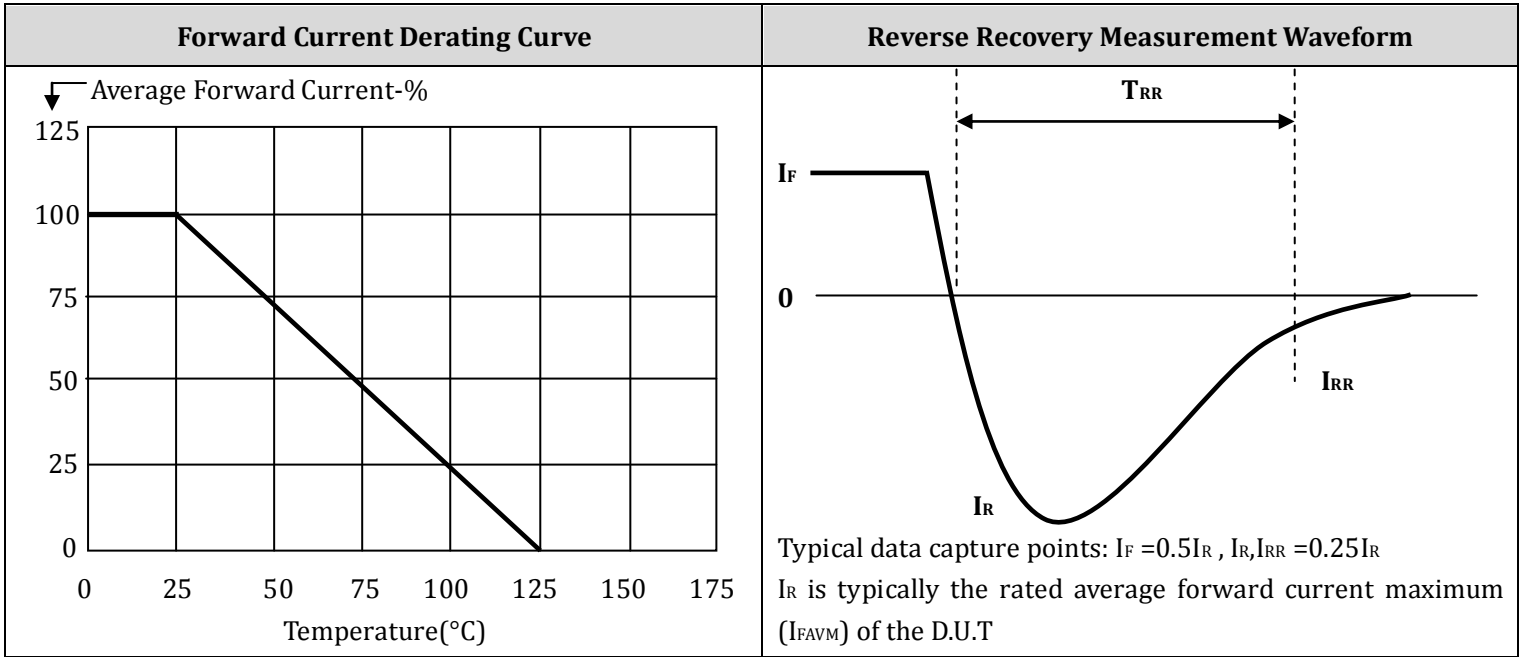
Applications:	HVGT Name:	Unit: (mm)
Air purification, negative ions. Electrostatic voltage doubling circuit. Copier and X-ray. Other high voltage rectifier circuits.	DO-308 Lead Diameter 0.6±0.03	
Mechanical Data:		
Case: epoxy resin molding. Terminal: welding axis. Net weight: 0.28 grams (approx).		

Maximum Ratings And Characteristics: (Absolute Maximum Ratings)

Items	Symbols	Condition	Data Value	Units
Repetitive Peak Reverse Voltage	V_{RRM}	$T_A=25^{\circ}C$	8.0	kV
Non-Repetitive Peak Reverse Voltage	V_{RSM}	$T_A=25^{\circ}C$	--	kV
Average Forward Current Maximum	I_{FAVM}	$T_A=25^{\circ}C$	10	mA
		$T_{OIL}=55^{\circ}C$	--	mA
Non-Repetitive Forward Surge Current	I_{FSM}	$T_A=25^{\circ}C$; 60Hz Half-Sine Wave; 8.3mS	1.0	A
Junction Temperature	T_J		125	$^{\circ}C$
Allowable Operation Case Temperature	T_C		-40~+125	$^{\circ}C$
Storage Temperature	T_{STG}		-40~+125	$^{\circ}C$

Electrical Characteristics: $T_A=25^{\circ}C$ (Unless Otherwise Specified)

Items	Symbols	Condition	Data value	Units
Maximum Forward Voltage Drop	V_{FM}	at $25^{\circ}C$; at I_{FAVM}	25	V
Maximum Reverse Current	I_{R1}	at $25^{\circ}C$; at V_{RRM}	2.0	μA
	I_{R2}	at $100^{\circ}C$; at V_{RRM}	5.0	μA
Maximum Reverse Recovery Time	T_{RR}	at $25^{\circ}C$; $I_F=0.5I_R$; $I_R=I_{FAVM}$; $I_{RR}=0.25I_R$	100	nS
Junction Capacitance	C_J	at $25^{\circ}C$; $V_R=0V$; $f=1MHz$	1.0	pF



	Type	Code	Cathode Mark
Marking	HV10G08	--	⋈

Packaging Standard		
Bulk Packaging	Label part number nothing "TR"	Package standard download link:
Tape Reel	Label part number has "TR"	http://www.hvgtsemi.com/newsv_490.html